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	Application No.	Applicant(s)
Notice of Allowability	10/001,557	LOJEK ET AL.
	Examiner	Art Unit
	lda M Soward	2822
The MAILING DATE of this communication apperature All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RI of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED in this app or other appropriate communication GHTS. This application is subject to	plication. If not included will be mailed in due course. THIS
1. A This communication is responsive to the Applicants' amend	dment filed December 29, 2003.	
2. X The allowed claim(s) is/are 3-7 and 9.		
3. $\boxtimes$ The drawings filed on <u>10-24-01</u> are accepted by the Exami	ner.	
4. ☐ Acknowledgment is made of a claim for foreign priority una) ☐ All b) ☐ Some* c) ☐ None of the:  1. ☐ Certified copies of the priority documents have 2. ☐ Certified copies of the priority documents have 3. ☐ Copies of the certified copies of the priority documents have International Bureau (PCT Rule 17.2(a)).  * Certified copies not received:  Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDONM THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.  5. ☐ A SUBSTITUTE OATH OR DECLARATION must be submin INFORMAL PATENT APPLICATION (PTO-152) which give 6. ☐ CORRECTED DRAWINGS (as "replacement sheets") must (a) ☐ including changes required by the Notice of Draftspers 1) ☐ hereto or 2) ☐ to Paper No./Mail Date  (b) ☐ including changes required by the attached Examiner's Paper No./Mail Date  Identifying indicia such as the application number (see 37 CFR 1. each sheet. Replacement sheet(s) should be labeled as such in the contraction of the deposition of t	been received.  been received in Application No cuments have been received in this is of this communication to file a reply of this application.  ENT of this application.  itted. Note the attached EXAMINER' as reason(s) why the oath or declarate the submitted.  on's Patent Drawing Review (PTO- as Amendment / Comment or in the Oct.  A Amendment / Comment or in the Oct.  B AMENDER OF THE COMMENT OF THE CO	national stage application from the complying with the requirements  S AMENDMENT or NOTICE OF tion is deficient.  948) attached  Office action of the back) of the complying with the front (not the back) of the complying in the submitted. Note the
attached Examiner's comment regarding REQUIREMENT	FOR THE DEPOSIT OF BIOLOGIC	AL MATERIAL.
Attachment(s)		
1. Notice of References Cited (PTO-892)		atent Application (PTO-152)
2. Notice of Draftperson's Patent Drawing Review (PTO-948)	6. ☐ Interview Summary Paper No./Mail Dat	
<ol> <li>Information Disclosure Statements (PTO-1449 or PTO/SB/0 Paper No./Mail Date</li> </ol>	8), 7. 🛭 Examiner's Amendr	nent/Comment
4. Examiner's Comment Regarding Requirement for Deposit		ent of Reasons for Allowance
of Biological Material		ARABIAN ATENT EXADIMER CENTER 2800

## **DETAILED ACTION**

This Office Action is in response to the Applicants' amendment filed December 29, 2003.

## **EXAMINER'S AMENDMENT**

An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

Authorization for this examiner's amendment was given in a telephone interview with Thomas Schneck on April 28, 2004.

The application has been amended as follows: "**comprising**" has been change to **including** in line 4 of the abstract.

- Claim 1. Cancelled
- Claim 2. Cancelled
- Claim 3. The non-volatile memory cell of claim 4 <u>9</u> wherein said <del>small spacer</del> resides connection conductive layer extends along a <u>said opposite</u> side <u>of said small sidewall spacer</u> and on top of said main floating gate region.
- Claim 4. The non-volatile memory cell of claim 3 9 wherein said first insulating portion is over the drain.

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Claim 6. The non-volatile memory cell of claim 4 9 wherein said small sidewall spacer resides connection conductive layer extends along a side and on top of said main floating gate region, said thin tunnel oxide having a portion covering the main floating gate region except for an opening therein, with the connecting conductive layer making contact with the main floating gate region through said opening.

Claim 7. The non-volatile memory cell of claim 4 <u>4</u> wherein said first insulating portion is over said drain extends across the memory cell.

Claim 8. Cancelled

Claim 9. (Newly Added) A non-volatile memory cell comprising:

a semiconductor substrate, with a drain and a source in said substrate;

a conductive floating gate formed on said substrate between said source and drain with a first insulating layer separating said floating gate from said substrate, said floating gate including a main floating gate region and a small sidewall spacer, said first insulating layer including a first insulating portion separating said small sidewall spacer from said substrate and from said main floating gate region, a second insulating portion separating said main floating gate region from said substrate, wherein said first insulating portion is a thin tunnel oxide that is thinner than said second insulating portion, said small sidewall spacer having a first vertical side contacting said thin tunnel oxide and an opposite side that is electrically coupled to said main floating gate region by a conductive connecting layer extending over said opposite side of said sidewall spacer and extending past said thin tunnel oxide to contact said main floating gate region;

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a control gate formed over said floating gate; and a second insulating layer separating said control gate and said floating gate.

## Allowable Subject Matter

Claims 3-9 are allowed.

## Conclusion

The prior art made of record and not relied upon is considered pertinent to applicant's disclosure.

The following patents are cited to further show the state of the art with respect to non-volatile memory cell structures:

Hsieh et al. (US 6,229,176 B1)

Lee (6,159,797)

Lim et al. (6,124,170)

Mehta et al. (6,060,766).

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Ida M Soward whose telephone number is 571-272-1845. The examiner can normally be reached on Monday - Thursday, 6:30 am to 5:00 pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Amir Zarabian can be reached on 571-272-1852. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

IMS April 28, 2004

AMIR ZARABIAN
SUPERVISORY PATENT EXAMINER
TECHNOLOGY CENTER 2800